

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC2970

DESCRIPTION

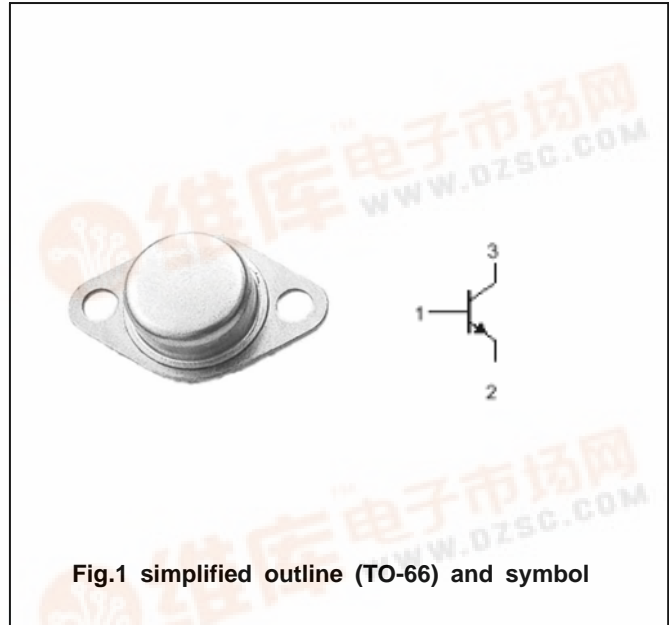
- With TO-66 package
- High voltage, high speed
- Low saturation voltage

APPLICATIONS

- For switching applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	300	V
V _{CEO}	Collector-emitter voltage	Open base	200	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		5	A
P _T	Total power dissipation	T _C =25°C	40	W
T _j	Junction temperature		175	°C
T _{stg}	Storage temperature		-55~175	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA ; I _B =0	200			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A; I _B =0.4A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A; I _B =0.4A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =300V ; I _E =0			100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			100	μ A
h _{FE}	DC current gain	I _C =2A ; V _{CE} =5V	15			

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PACKAGE OUTLINE

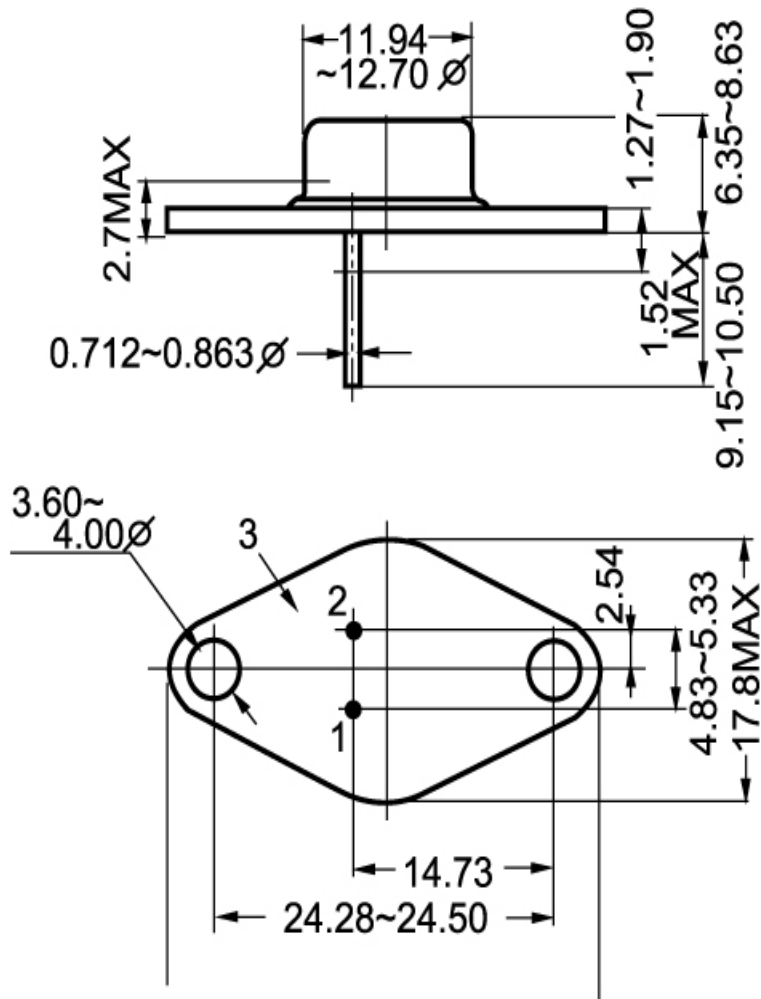


Fig.2 Outline dimensions